

# PQMD10

# NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

4 November 2015

**Product data sheet** 

# 1. General description

NPN/PNP double Resistor-Equipped Transistors (RET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PQMH10

## 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Low package height of 0.37 mm
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

# 3. Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor;	Per transistor; for the PNP transistor with negative polarity							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	100	mA	
Per transistor;	Per transistor; for the PNP transistor with negative polarity							
R1	bias resistor 1	T <sub>amb</sub> = 25 °C	[1]	1.54	2.2	2.86	kΩ	
R2/R1	bias resistor ratio		[1]	17	21	26		

[1] See section "Test information" for resistor calculation and test conditions.



# NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1	500	O1 I2 GND2
2	I1	input ( base) TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ \end{bmatrix}$	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2		TR1 TR2
5	12	input ( base) TR2	3 4	R2 R1
6	O1	output (collector) TR1	Transparent top view	
7	O1	output (collector) TR1	DFN1010B-6 (SOT1216)	GND1 I1 O2 aaa-007379
8	O2	output (collector) TR2		dad 557575

# 6. Ordering information

Table 3. Ordering information

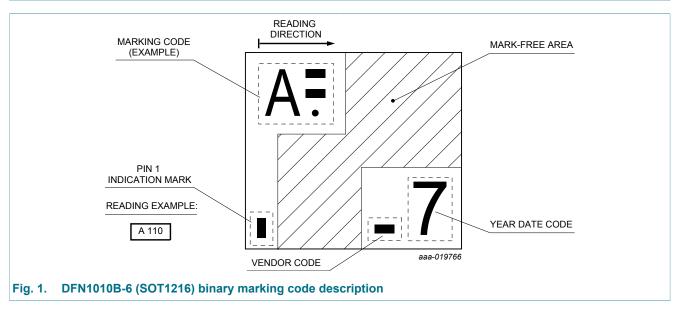
Type number	Package					
	Name	Description	Version			
PQMD10	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216			

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# 7. Marking

Table 4. Marking codes

Type number	Marking code
PQMD10	B 010



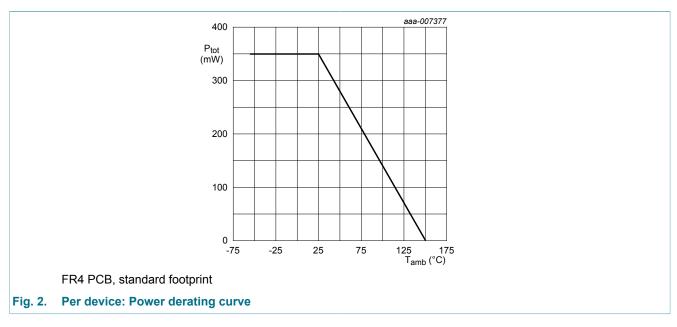
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor; for the PNP transistor with	negative polarity				
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
VI	input voltage	TR1; positive		-	12	V
		TR1; negative		-	-5	V
		TR2; positive		-	5	V
		TR2; negative		-	-12	V
lo	output current			-	100	mA
I <sub>CM</sub>	peak collector current	t <sub>p</sub> ≤ 1 ms; single pulse		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	230	mW
Per device			,			
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	350	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



PQMD10

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NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

# 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	543	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	357	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

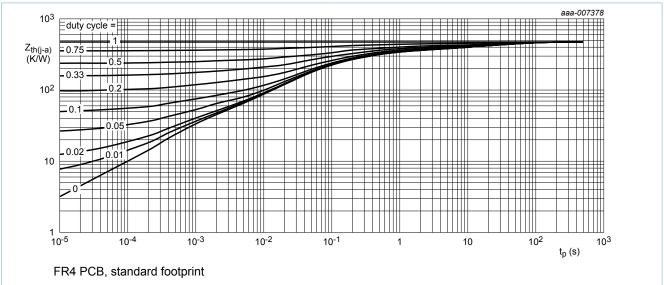


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

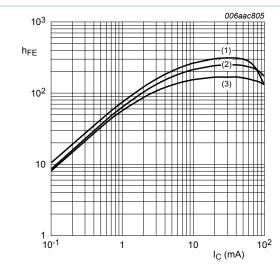
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor; for the PNP transistor	with negative polarity					
I <sub>CBO</sub>	collector-base cut-off current (emitter open)	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	1	μA
	current (base open)	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 150 °C		-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current (collector open)	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	180	μA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; $T_{amb}$ = 25 °C		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE}$ = 5 V; $I_{C}$ = 100 $\mu$ A; $T_{amb}$ = 25 °C		-	0.6	0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V; } I_{C} = 5 \text{ mA; } T_{amb} = 25 \text{ °C}$		1.1	0.75	-	V
R1	bias resistor 1	T <sub>amb</sub> = 25 °C	[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	17	21	26	
C <sub>C</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; f = 1 \text{ MHz};$ $T_{amb} = 25 \text{ °C}; TR1 \text{ (NPN)}$		-	-	2.5	pF
		$V_{CB}$ = -10 V; $I_{E}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C; TR2 (PNP)		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C; TR1 (NPN)	[2]	-	230	-	MH
		$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C; TR2 (PNP)	[2]	-	180	-	MHz

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions.

<sup>[2]</sup> Characteristics of built-in transistor

#### NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$



$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$



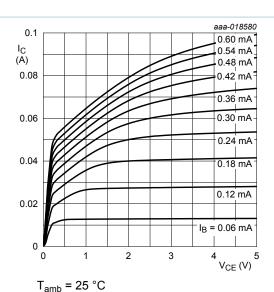
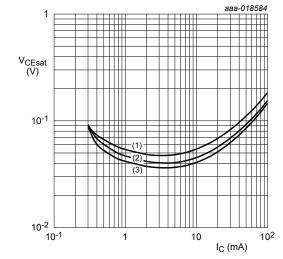


Fig. 5. NPN transistor: Collector current as a function of collector-emitter voltage; typical values



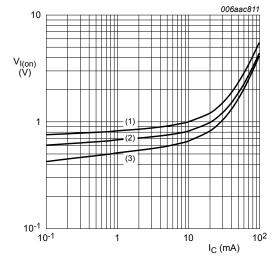
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 6. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = 0.3 \text{ V}$$

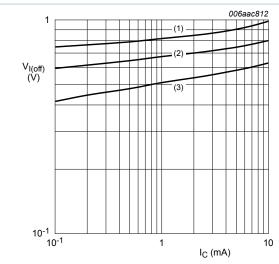
(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. NPN transistor: On-state input voltage as a function of collector current; typical values

#### NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$



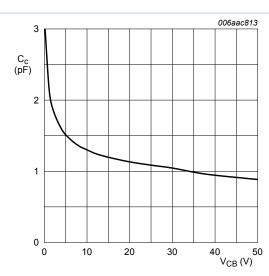
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

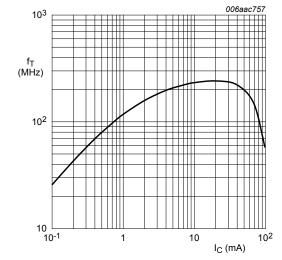
(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. NPN transistor: Off-state input voltage as a function of collector current; typical values



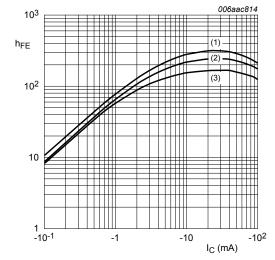
 $f = 1 MHz; T_{amb} = 25 °C$ 

Fig. 9. NPN transistor: Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE}$  = 5 V;  $T_{amb}$  = 25 °C

Fig. 10. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



 $V_{CE} = -5 V$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 11. PNP transistor: DC current gain as a function of collector current; typical values

#### NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

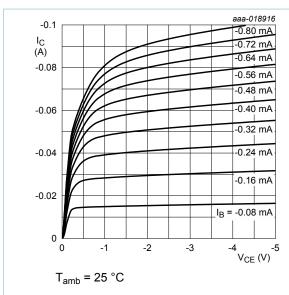
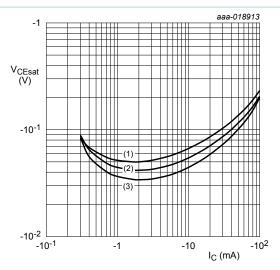


Fig. 12. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



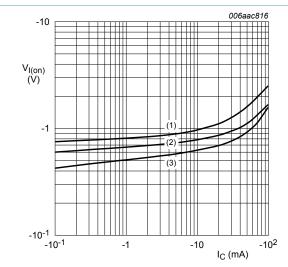
 $I_{\rm C}/I_{\rm B}=20$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



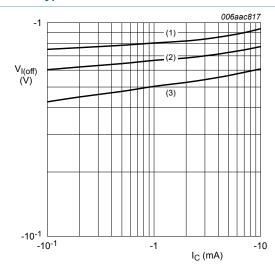
 $V_{CE}$  = -0.3 V

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 14. PNP transistor: On-state input voltage as a function of collector current; typical values



 $V_{CE} = -5 V$ 

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 15. PNP transistor: Off-state input voltage as a function of collector current; typical values

#### NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

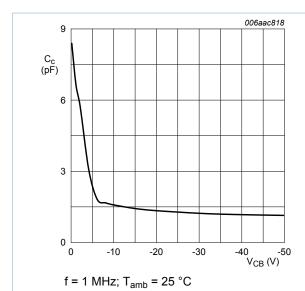
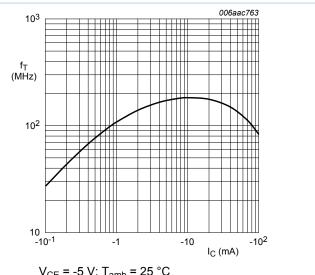


Fig. 16. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE}$  = -5 V;  $T_{amb}$  = 25 °C

Fig. 17. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

## 11. Test information

# 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

#### 11.2 Resistor calculation

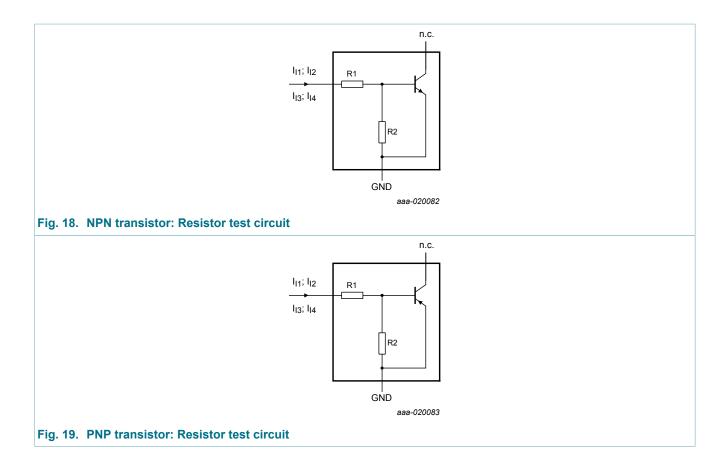
Calculation of bias resistor 1 (R1)

$$RI = \frac{V(I_{12}) - V(I_{11})}{I_{12} - I_{11}}$$

Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

## NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$



## 11.3 Resistor test conditions

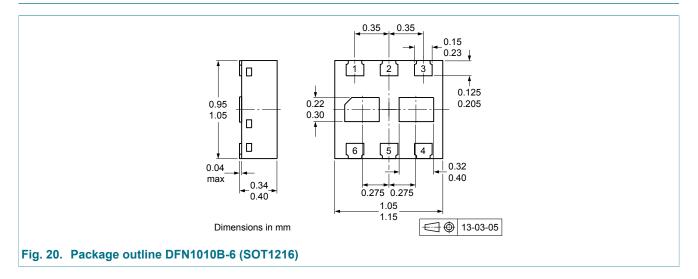
Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions			
		I <sub>I1</sub>	I <sub>I2</sub>	I <sub>I3</sub>	I <sub>14</sub>
2.2	47	90 μΑ	140 μΑ	-55 μΑ	-105 μΑ

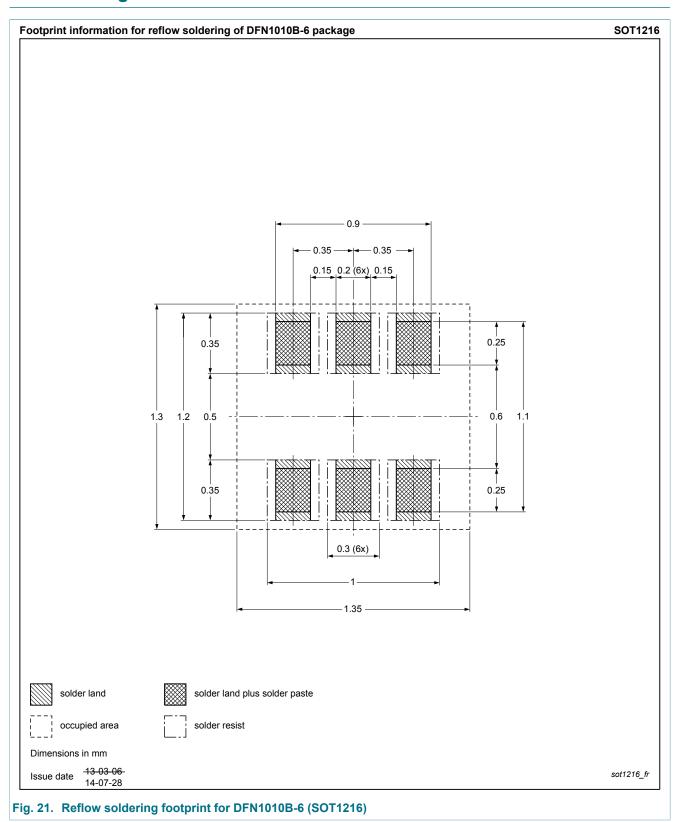
NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

# 12. Package outline



NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

# 13. Soldering



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NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PQMD10 v.1	20151104	Product data sheet	-	-

#### NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

# 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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